Attorney's Docket No.: 10559-881001/P17483 Intel Corporation

THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yan Borodovsky Art Unit: 1756

Filed : October 7, 2003
Assignee : Intel Corporation

Title : COMPOSITE OPTICAL LITHOGRAPHY METHOD FOR PATTERNING

LINES OF SUBSTANTIALLY EQUAL WIDTH

## Mail Stop Amendment

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

## INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicants call attention to the attached Information Disclosure Statement and documents listed on form PTO-1449.

This filing is being made before the receipt of a first Office action on the merits. No fee is required.

The documents are in the English language; hence no concise explanation is necessary per Rule 98(a)(3).

Consideration of the foregoing and enclosures plus the return of a copy of the enclosed form PTO-1449 with the

## CERTIFICATE OF MAILING BY FIRST CLASS MAIL

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March 29, 2005

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Applicant : Yan Borodovsky Attorney's Docket No.:10559-881001 Serial No.: 10/681,031

Filed : October 7, 2003

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Examiner's initials in the left column per MPEP 609 are earnestly solicited along with an early action on the merits.

Please apply any additional charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: March 29, 2005

Scott C. Harris Reg. No. 32,030

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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Traverpark Office	Attorney's Docket No. 10559-881001	Application No. 10/681,031
by Api	losure Statement Solicant	Applicant Yan Borodovsky	
(Use several she	ets if necessary MAR 3 1 2005	Filing Date October 7, 2003	Group Art Unit 1756

	U.S. Patent Documents						
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AÇ						
	AD						

	Foreign Patent Documents or Published Foreign Patent Applications							
Examiner	Desig.	Document	Publication	Country or			Translation	
Initial	ID	Number	Date	Patent Office	Class	Subclass	Yes	No
,	AE							
	AF							
	AG							

	Other Documents (include Author, Title, Date, and Place of Publication)				
Examiner Initial	Desig. ID	Document			
mittal	AH	M. Fritze, et al., "Gratings of regular arrays and trim exposures for ultralarge scale integrated circuit phase-shift lithography", J. of Vacuum Science & Technology B, 19(6):2366-2370, Nov/Dec 2001.			
	AI	J.A. Hoffnagle, et al., "Liquid immersion deep-ultraviolet interferometric lithography", J. of Vacuum Science & Technology B, 17(6):3306-3309, Nov/Dec 1999.			
	AJ	Marc D. Levenson, et al., "Exposing the DUV SCAAM – 75 nm Imaging on the Cheap!", Proc. of SPIE: Design, Process Integration, and Characterization for Microelectronics, 4692:288-297, March 2002.			
	AK	Alex K. Raub, et al., "Deep UV immersion interferometric lithography", Proc. of SPIE: Optical Microlithography XVI, 5040:667-678, Feb. 2003.			
	AL	Bruce W. Smith, et al., "Water immersion optical lithography at 193 nm", J. Microlith., Microfab., Microsyst., 3(1):44-51, Jan. 2004.			
	AM	Akiyoshi Susuki, et al., "Multilevel imaging system realizing k <sub>1</sub> +=0.3 lithography", <i>Proc. of SPIE:</i> Optical Microlithography XII, 3679:396-407, Mar. 1999.			
	AN	M. Switkes, et al., "Extending optics to 50 nm and beyond with immersion lithography", J. of Vacuum Science & Technology B, 21(6):2794-2799, Nov/Dec 2003.			
	AO	Brian Tyrrell, et al., "Investigation of the physical and practical limits of dense-only phase shift lithography for circuit feature definition", <i>J. Microlith., Microfab., Microsyst.</i> , 1(3):244-252, Oct. 2002.			
	AP	Saleem H. Zaidi, et al., "Multiple exposure interferometric lithography", Proc. of SPIE: Optical Microlithography VII, 2197:869-875, Mar. 1994.			
	AQ	M. Fritze, et al., "Preprint of poster presentation entitled "High-Throughput Hybrid Optical Maskless Lithography: All-Optical 32-nm Node Imaging,", Presented at SPIE Microlithography 2005, San Jose, California, USA, March 3, 2005.			

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation next communication to applicant.	if not in conformance and not considered. Include copy of this form with